

isc Silicon NPN RF Transistor

2SC2757

DESCRIPTION

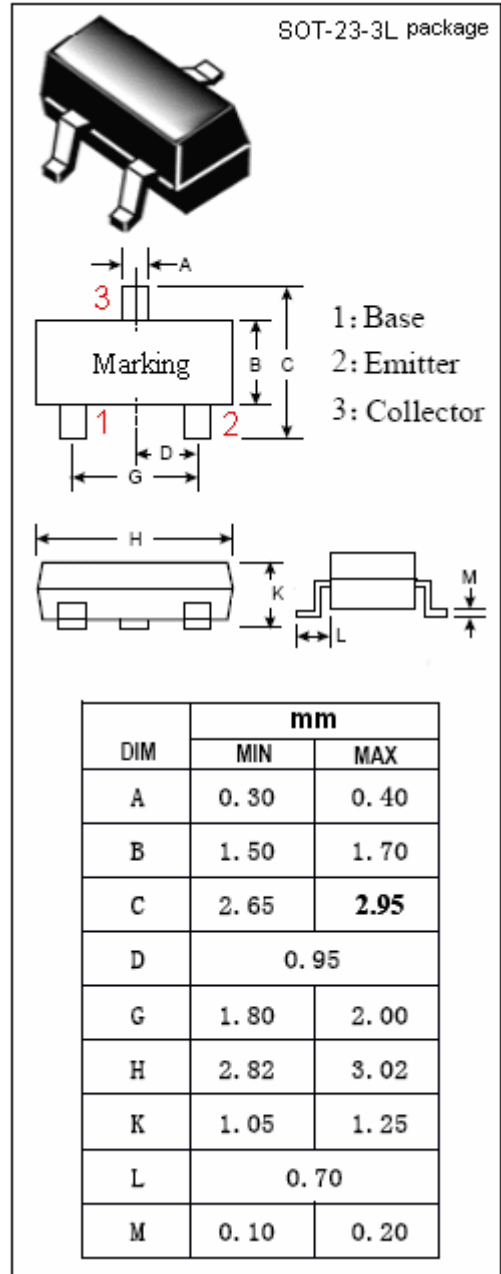
- Low Noise
- High Current-Gain Bandwidth Product

APPLICATIONS

- Designed for use in VHF RF amplifier, local oscillator, mixer.

ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CBO}	Collector-Base Voltage	30	V
V _{CEO}	Collector-Emitter Voltage	15	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current-Continuous	50	mA
P _C	Collector Power Dissipation @T _C =25°C	0.15	W
T _J	Junction Temperature	125	°C
T _{stg}	Storage Temperature Range	-55~125	°C



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ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=10\text{mA}$; $I_B=1\text{mA}$			0.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB}=12\text{V}$; $I_E=0$			0.1	μA
h_{FE}	DC Current Gain	$I_C=5\text{mA}$; $V_{CE}=10\text{V}$	60		240	
f_T	Current-Gain—Bandwidth Product	$I_C=5\text{mA}$; $V_{CE}=10\text{V}$	800	1100		MHz
C_{OB}	Output Capacitance	$I_E=0$; $V_{CB}=10\text{V}$; $f=1.0\text{MHz}$			1.5	pF
$\tau_{bb'} \cdot CC$	Base Time Constant	$I_C=5\text{mA}$; $V_{CB}=10\text{V}$; $f=31.9\text{MHz}$		10	15	ps

◆ h_{FE} Classifications

Marking	T32	T33	T34
h_{FE}	60-120	90-180	120-240